

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or unavteries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor and is officers, employees, uniotificated use, even if such claim any manner.



FDA18N50 N-Channel UniFET[™] MOSFET 500 V, 19 A, 265 mΩ

Features

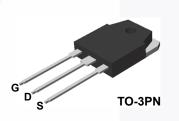
- $R_{DS(on)}$ = 265 m Ω (Max.) @ V_{GS} = 10 V, I_D = 9.5 A
- Low Gate Charge (Typ. 45 nC)
- Low C_{rss} (Typ. 25 pF)
- 100% Avalanche Tested

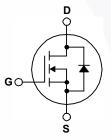
Applications

- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FDA18N50	Unit	
V _{DSS}	Drain-Source Voltage			500	V	
ID	Drain Current	- Continuous ($T_C = 25^{\circ}C$) - Continuous ($T_C = 100^{\circ}C$)		19 11.4	A A	
I _{DM}	Drain Current	- Pulsed	(Note 1)	76	А	
V _{GSS}	Gate-Source voltage			±30	V	
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	945	mJ	
I _{AR}	Avalanche Current		(Note 1)	19	А	
E _{AR}	Repetitive Avalanche Energy		(Note 1)	23	mJ	
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	4.5	V/ns	
P _D	Power Dissipation	(T _C = 25°C) - Derate above 25°C		239 1.92	W W/°C	
T _{J,} T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C		
TL	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C		

Thermal Characteristics

Symbol	Parameter	FDA18N50	Unit	
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.52	°C/W	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	C/W	

1

N-Channel UniFET ^{1M} MOSFET	Unit V V/°C μΑ μΑ nA nA N Ω S	
SFET	V Ω	
		S
		pF
		pF
		pF

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDA18N50	FDA18N50	TO-3PN	Tube	N/A	30 units

Electrical Characteristics $T_{C} = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter Conditions		Min.	Тур.	Max	Unit
Off Charac	teristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250\mu A$				V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu A$, Referenced to $25^{\circ}C$		0.5		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500V, V_{GS} = 0V$ $V_{DS} = 400V, T_{C} = 125^{\circ}C$			1 10	μΑ μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V			-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 9.5A		0.220	0.265	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40V, I _D = 9.5A		25		S
Dynamic C	Characteristics				1	
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz		2200	2860	pF
C _{oss}	Output Capacitance			330	430	pF
C _{rss}	Reverse Transfer Capacitance	_		25	40	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 250V, I _D = 19A		55	120	ns
t _r	Turn-On Rise Time	$R_{G} = 25\Omega$		165	340	ns
t _{d(off)}	Turn-Off Delay Time		-	95	200	ns
t _f	Turn-Off Fall Time	(Note 4)		90	190	ns
Qg	Total Gate Charge	V _{DS} = 400V, I _D = 19A		45	60	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10V		12.5		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		19		nC
Drain-Sour	rce Diode Characteristics and Maximur	n Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				19	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				76	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 19A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 19A		500		ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt =100A/μs		5.4		μC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. L = 4.7mH, I_{AS} = 19A, V_DD = 50V, R_G = 25 Ω , Starting T_J = 25°C

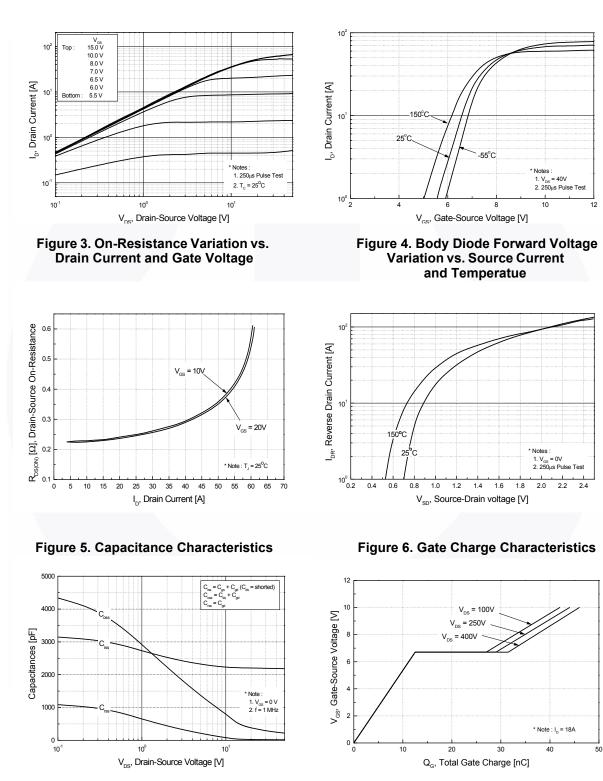
3. I_{SD} \leq 19A, di/dt \leq 200A/µs, V_{DD} \leq BV_{DSS}, Starting T_J = 25°C

4. Essentially Independent of Operating Temperature Typical Characteristics

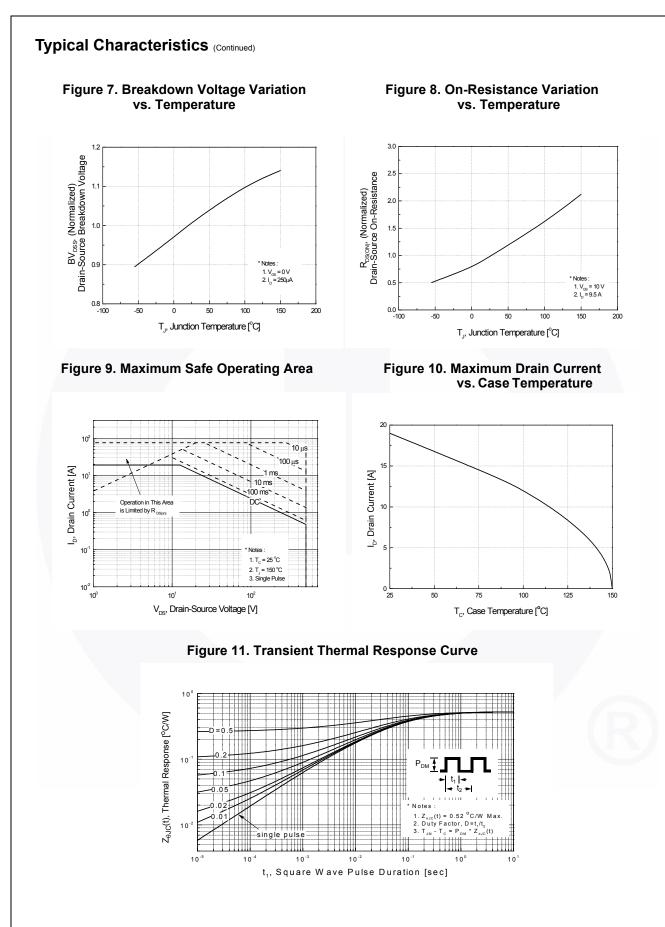
Typical Characteristics



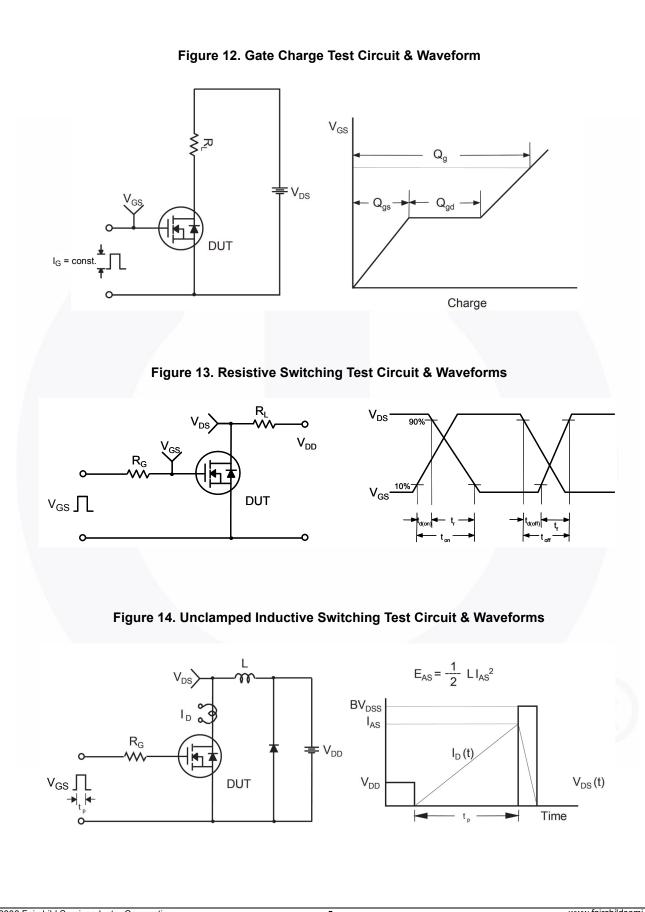
Figure 2. Transfer Characteristics



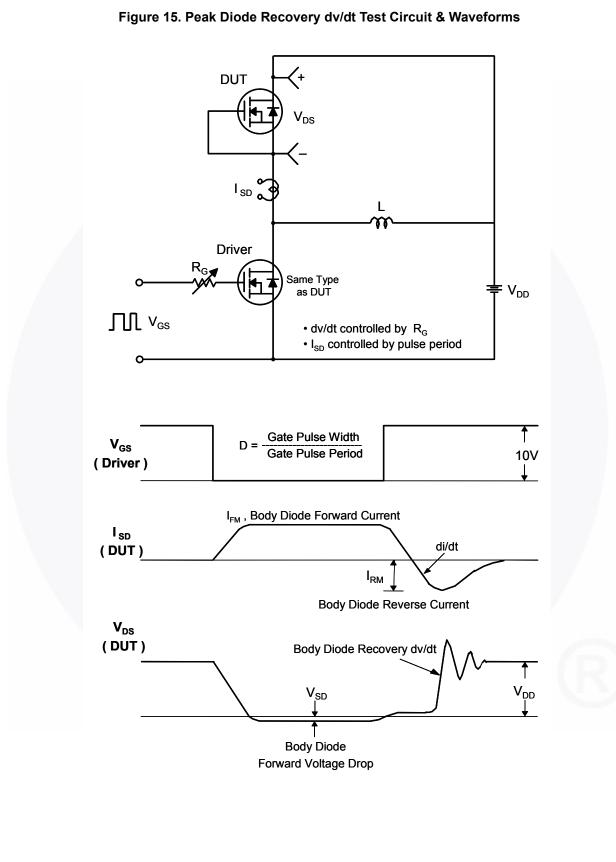
FDA18N50 — N-Channel UniFETTM MOSFET

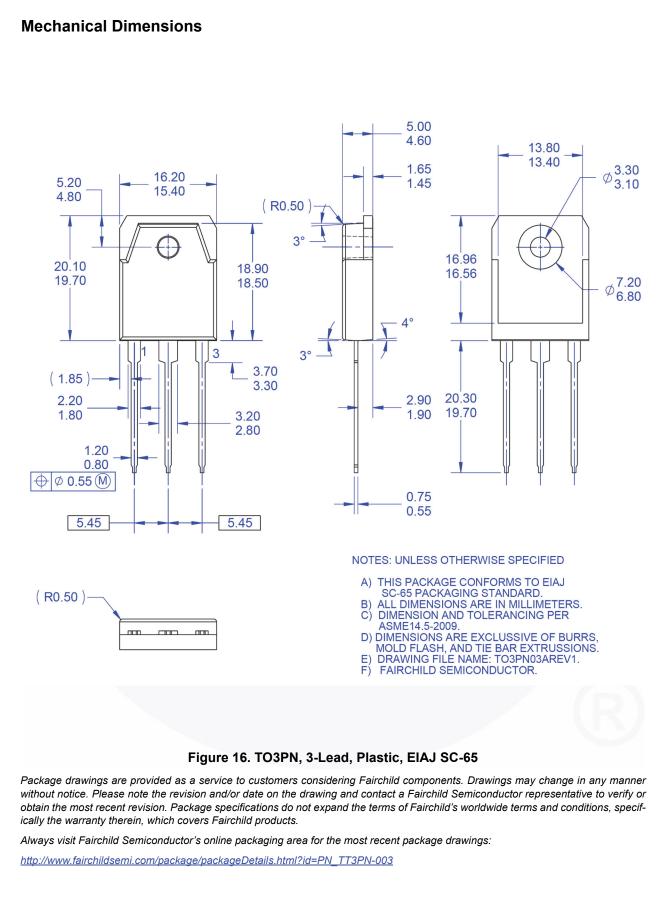


4



5







ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor haves against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death a

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor: FDA18N50